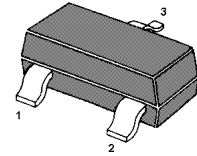
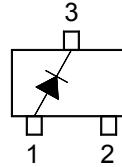


Silicon Epitaxial Planar Diode

Low leakage switching diode

Features

- Plastic SMD package
- Low leakage current



SOT-23 Plastic Package

Application

- Low leakage current applications in surface mounted circuits.

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	215	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	4	A
		1	
		0.5	
Power Dissipation	P_{tot}	250	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	-	0.9	V
	V_F	-	1	V
	V_F	-	1.1	V
	V_F	-	1.25	V
Reverse Current at $V_R = 75\text{ V}$ at $V_R = 75\text{ V}, T_j = 150\text{ }^\circ\text{C}$	I_R	-	5	nA
		-	80	
Diode Capacitance at $V_R = 0, f = 1\text{ MHz}$	C_d	2	-	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}, R_L = 100\text{ }\Omega, i_{rr} = 0.1 I_R$	t_{rr}	-	3	μs

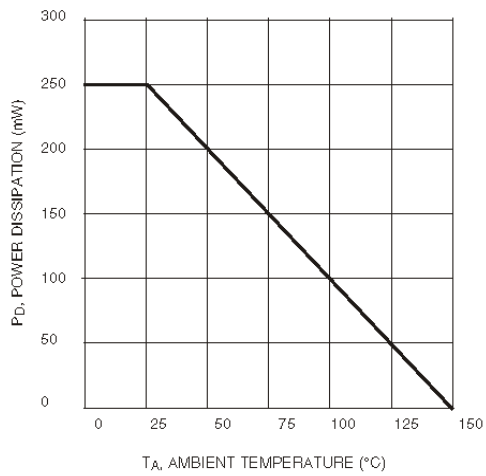


Fig. 1 Power Derating Curve

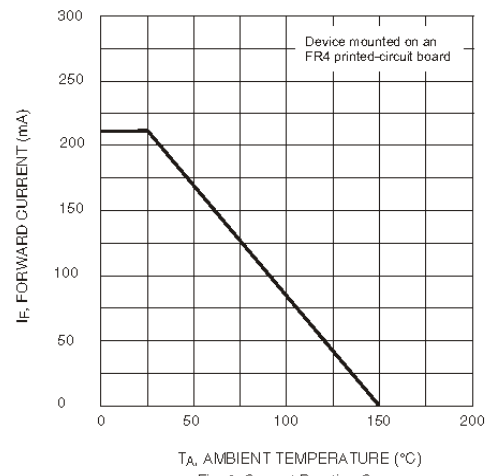


Fig. 2 Current Derating Curve

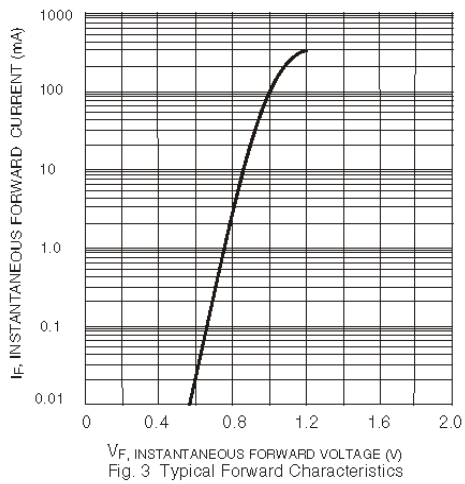


Fig. 3 Typical Forward Characteristics

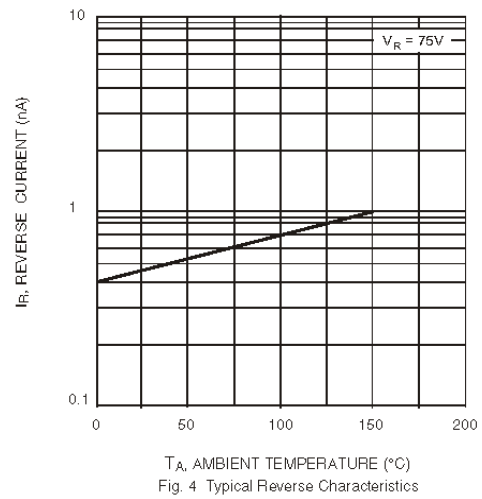


Fig. 4 Typical Reverse Characteristics